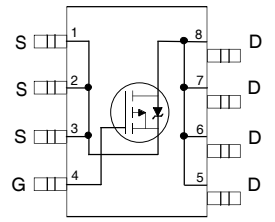
International
IOR Rectifier

PD - 95245

IRF7606PbF

HEXFET® Power MOSFET

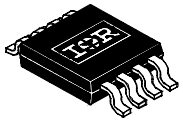
- Generation V Technology
- Ultra Low On-Resistance
- P-Channel MOSFET
- Very Small SOIC Package
- Low Profile (<1.1mm)
- Available in Tape & Reel
- Fast Switching
- Lead-Free



Top View

V_{DSS} = -30V

$R_{DS(on)}$ = 0.09Ω


Micro8

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The new Micro8 package, with half the footprint area of the standard SO-8, provides the smallest footprint available in an SOIC outline. This makes the Micro8 an ideal device for applications where printed circuit board space is at a premium. The low profile (<1.1mm) of the Micro8 will allow it to fit easily into extremely thin application environments such as portable electronics and PCMCIA cards.

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain-Source Voltage	-30	V
I_D @ T_A = 25°C	Continuous Drain Current, V_{GS} @ -10V	-3.6	A
I_D @ T_A = 70°C	Continuous Drain Current, V_{GS} @ -10V	-2.9	
I_{DM}	Pulsed Drain Current①	-29	
P_D @T_A = 25°C	Maximum Power Dissipation④	1.8	W
P_D @T_A = 70°C	Maximum Power Dissipation ④	1.1	W
	Linear Derating Factor	14	mW/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
V_{GSM}	Gate-to-Source Voltage Single Pulse tp<10µS	30	V
dv/dt	Peak Diode Recovery dv/dt ②	-5.0	V/ns
T_J , T_{STG}	Junction and Storage Temperature Range	-55 to + 150	°C
	Soldering Temperature, for 10 seconds	240 (1.6mm from case)	

Thermal Resistance

	Parameter	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient ④	70	°C/W

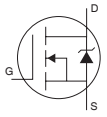
All Micro8 Data Sheets reflect improved Thermal Resistance, Power and Current -Handling Ratings- effective only for product marked with Date Code 505 or later .

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-30	—	—	V	V_{GS} = 0V, I_D = 250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.024	—	V/°C	Reference to 25°C, I_D = -1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	0.075	0.09	Ω	V_{GS} = - 10V, I_D = -2.4A ③
		—	0.130	0.15		V_{GS} = -4.5V, I_D = -1.2A ③
$V_{GS(th)}$	Gate Threshold Voltage	-1.0	—	—	V	V_{DS} = V_{GS}, I_D = -250µA
g_{fs}	Forward Transconductance	2.3	—	—	S	V_{DS} = -10V, I_D = -1.2A
I_{DSS}	Drain-to-Source Leakage Current	—	—	-1.0	µA	V_{DS} = -24V, V_{GS} = 0V
		—	—	-25		V_{DS} = -24V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	V_{GS} = -20V
	Gate-to-Source Reverse Leakage	—	—	100		V_{GS} = 20V
Q_g	Total Gate Charge	—	20	30	nC	I_D = -2.4A
Q_{gs}	Gate-to-Source Charge	—	2.1	3.1		V_{DS} = -24V
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	7.6	11		V_{GS} = -10V, See Fig. 9 ③
$t_{d(on)}$	Turn-On Delay Time	—	13	—	ns	V_{DD} = -10V
t_r	Rise Time	—	20	—		I_D = -2.4A
$t_{d(off)}$	Turn-Off Delay Time	—	43	—		R_G = 6.0Ω
t_f	Fall Time	—	39	—		R_D = 4.0Ω ③
C_{iss}	Input Capacitance	—	520	—	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	—	300	—		V_{DS} = -25V
C_{rss}	Reverse Transfer Capacitance	—	140	—		f = 1.0MHz, See Fig. 8

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-1.8	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-29		
V_{SD}	Diode Forward Voltage	—	—	-1.2	V	T_J = 25°C, I_S = -2.4A, V_{GS} = 0V ③
t_{rr}	Reverse Recovery Time	—	43	64	ns	T_J = 25°C, I_F = -2.4A
Q_{rr}	Reverse Recovery Charge	—	50	76	nC	di/dt = -100A/µs ③



Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 10)

② I_{SD} ≤ -2.4A, di/dt ≤ -130A/µs, V_{DD} ≤ $V_{(BR)DSS}$, T_J ≤ 150°C

③ Pulse width ≤ 300µs; duty cycle ≤ 2%.

④ Surface mounted on FR-4 board, t ≤ 10sec.

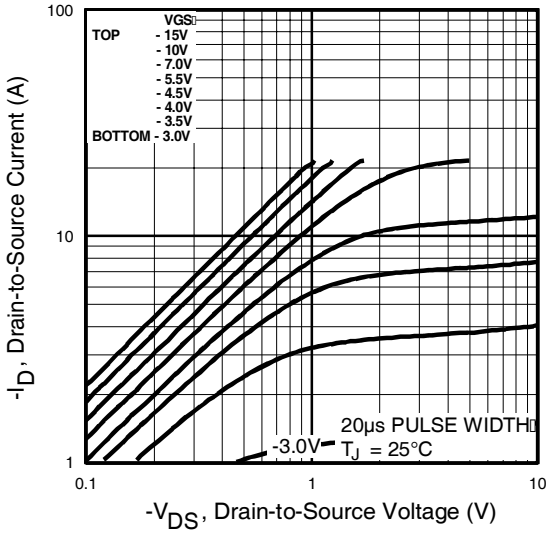


Fig 1. Typical Output Characteristics

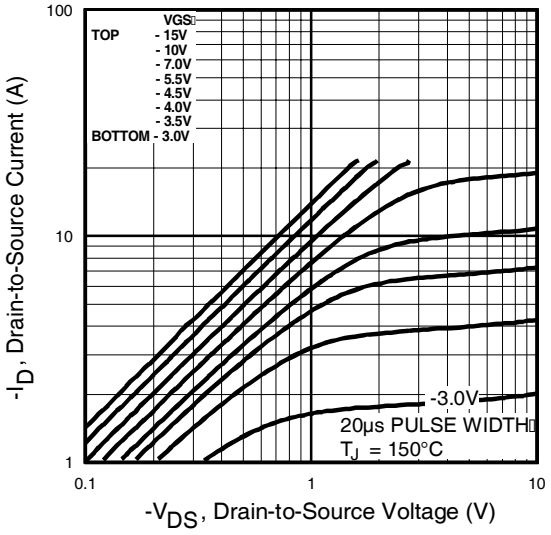


Fig 2. Typical Output Characteristics

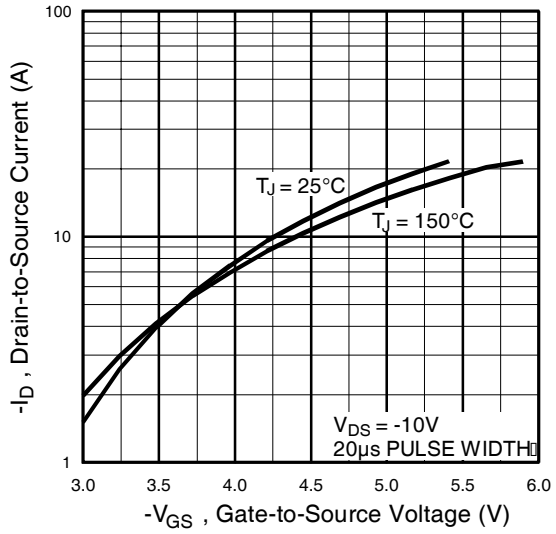


Fig 3. Typical Transfer Characteristics

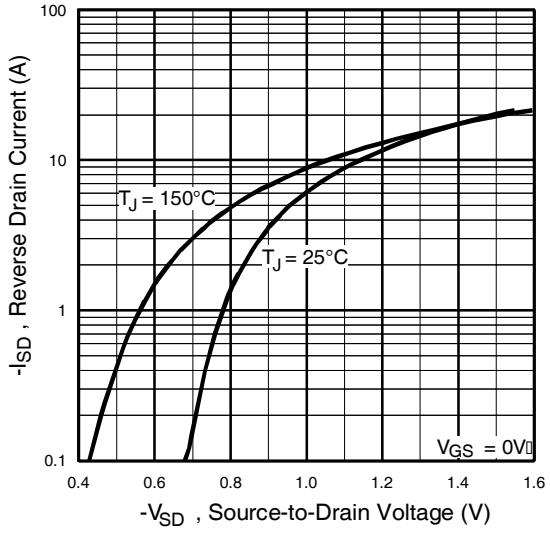


Fig 4. Typical Source-Drain Diode Forward Voltage

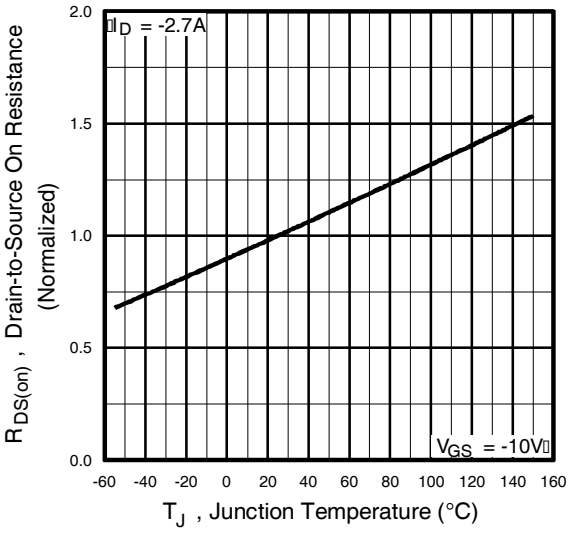


Fig 5. Normalized On-Resistance Vs. Temperature

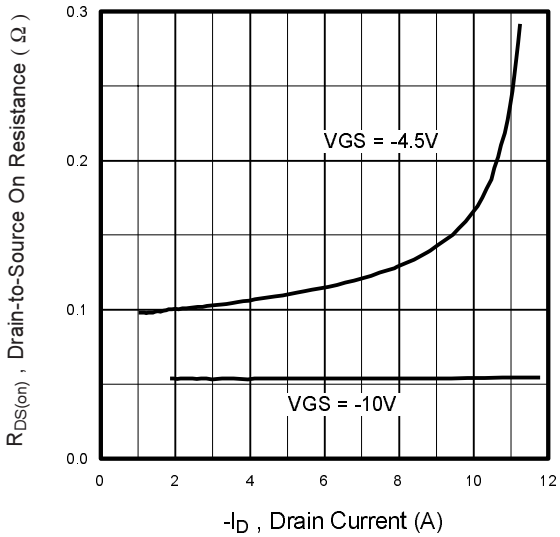


Fig 6. Typical On-Resistance Vs. Drain Current

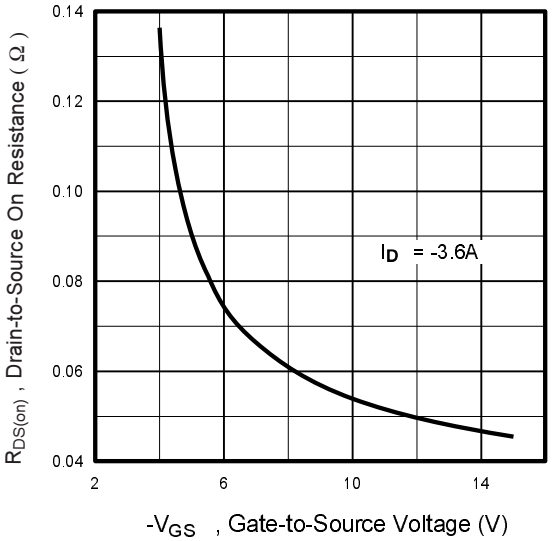


Fig 7. Typical On-Resistance Vs. Gate Voltage

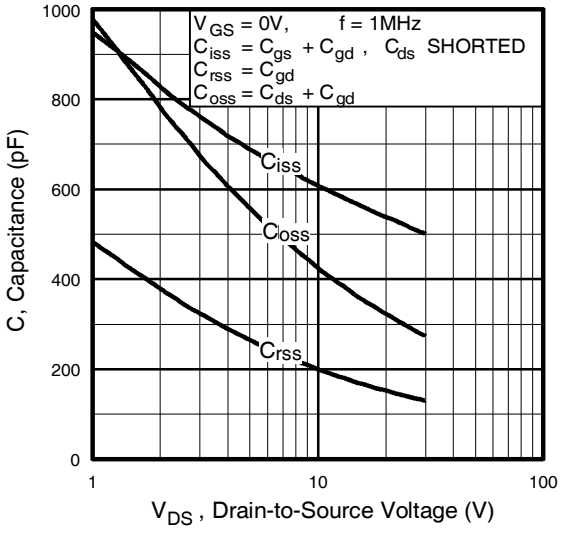


Fig 8. Typical Capacitance Vs. Drain-to-Source Voltage

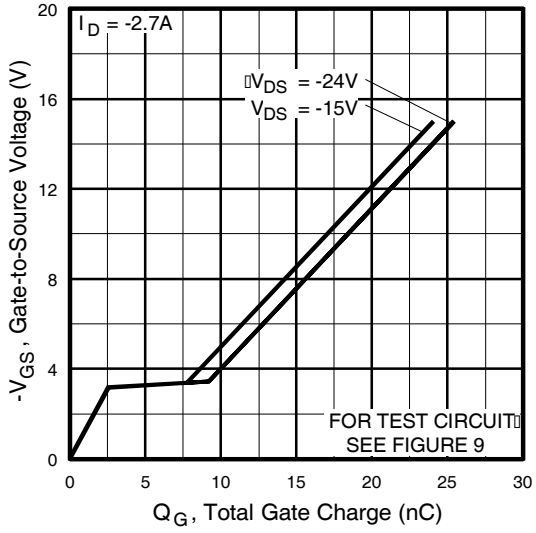


Fig 9. Typical Gate Charge Vs. Gate-to-Source Voltage

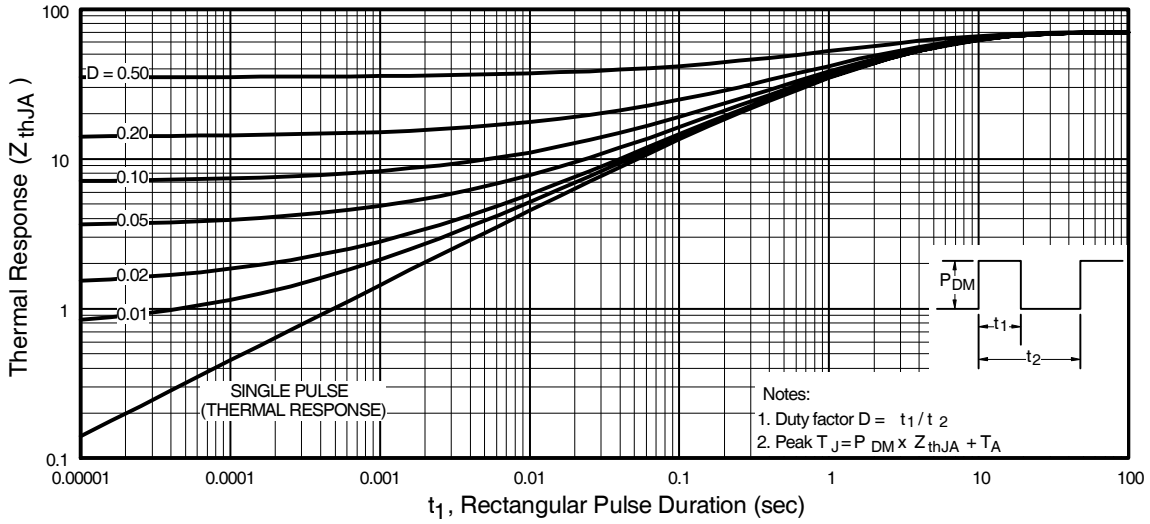
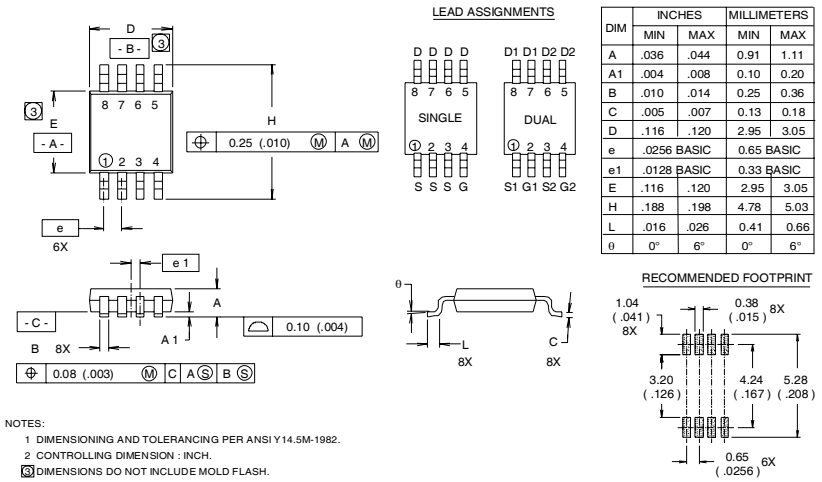


Fig 10. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

Micro8 Package Outline

Dimensions are shown in milimeters (inches)

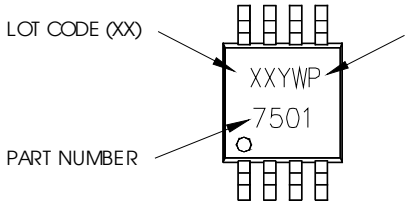


DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.036	.044	0.91	1.11
A1	.004	.008	0.10	0.20
B	.010	.014	0.25	0.36
C	.005	.007	0.13	0.18
D	.116	.120	2.95	3.05
e	.0256 BASIC		0.65 BASIC	
e1	.0128 BASIC		0.33 BASIC	
E	.116	.120	2.95	3.05
H	.188	.198	4.78	5.03
L	.016	.026	0.41	0.66
θ	0°	6°	0°	6°

NOTES:
1 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1982.
2 CONTROLLING DIMENSION : INCH.
3 DIMENSIONS DO NOT INCLUDE MOLD FLASH.

Micro8 Part Marking Information

EXAMPLE: THIS IS AN IRF7501



WW = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR

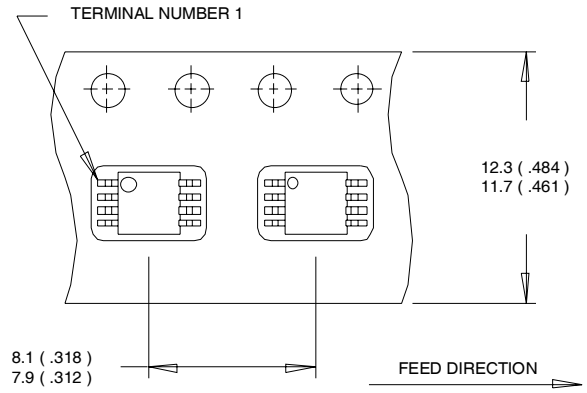
YEAR	Y	WORK WEEK	W
2001	1	01	A
2002	2	02	B
2003	3	03	C
2004	4	04	D
2005	5		
2006	6		
2007	7		
2008	8		
2009	9		
2010	0	24	X
		25	Y
		26	Z

WW = (27-52) IF PRECEDED BY A LETTER

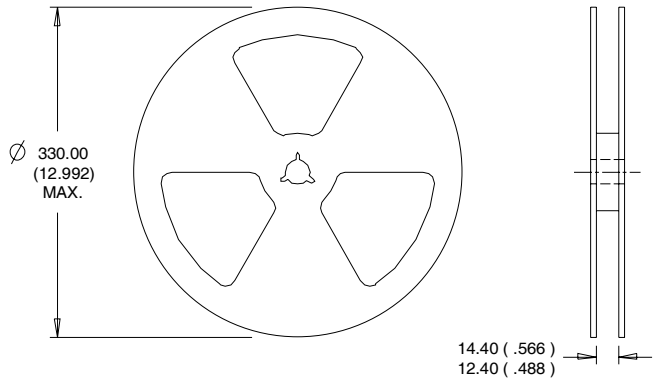
YEAR	Y	WORK WEEK	W
2001	A	27	A
2002	B	28	B
2003	C	29	C
2004	D	30	D
2005	E		
2006	F		
2007	G		
2008	H		
2009	J		
2010	K	50	X
		51	Y
		52	Z

Micro8 Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES:
1. OUTLINE CONFORMS TO EIA-481 & EIA-541.
2. CONTROLLING DIMENSION : MILLIMETER.



NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
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Data and specifications subject to change without notice.
This product has been designed and qualified for the Consumer market.
Qualification Standards can be found on IR's Web site.

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http://moschip.ru/get-element

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